

Silicon NPN Power Transistors

2SD826

DESCRIPTION

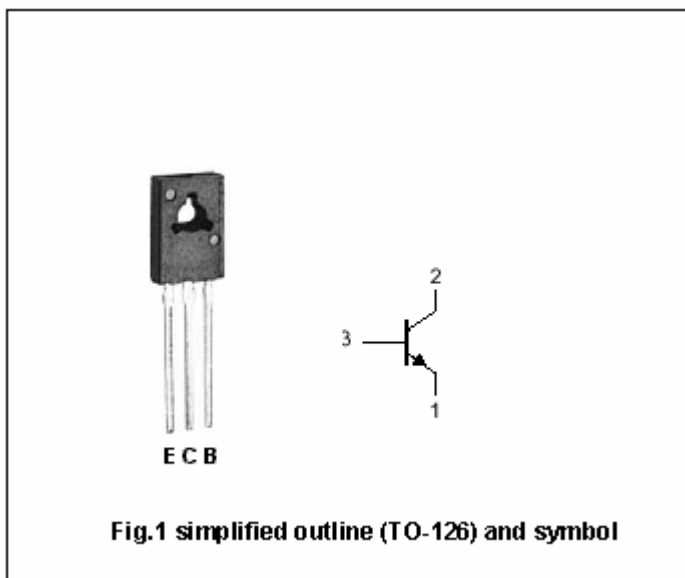
- With TO-126 package
- Low collector saturation voltage
- High DC current gain
- Large current capacity

APPLICATIONS

- For 3V, 6V strobe applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	60	V
V_{CEO}	Collector-emitter voltage	Open base	20	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		5	A
I_{CM}	Collector current-peak	t=100ms	8	A
P_C	Collector power dissipation	$T_a=25$	1.0	W
		$T_C=25$	10	
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEsat}	Collector-emitter saturation voltage	I _C =3A; I _B =60mA(pulse)			0.5	V
V _{BEsat}	Base-emitter saturation voltage	I _C =3A; I _B =60mA(pulse)			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =50V; I _E =0			1.0	μA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			1.0	μA
h _{FE-1}	DC current gain	I _C =0.5A; V _{CE} =2V	120		560	
h _{FE-2}	DC current gain	I _C =3A; V _{CE} =2V(pulse)	95			
f _T	Transition frequency	I _C =50mA; V _{CE} =10V		120		MHz
C _{OB}	Collector output capacitance	f=1MHz; V _{CB} =10V		45		pF

Switching times

t _{on}	Turn-on time	I _C =2A; I _{B1} =-I _{B2} =0.2A V _{CC} =10V; R _L =5		30		ns
t _{stg}	Storage time			300		ns
t _f	Fall time			40		ns

◆ h_{FE-1} Classifications

E	F	G
120-200	160-320	280-560

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PACKAGE OUTLINE

